



7NM70

Power MOSFET

7.0A, 700V N-CHANNEL SUPER-JUNCTION MOSFET

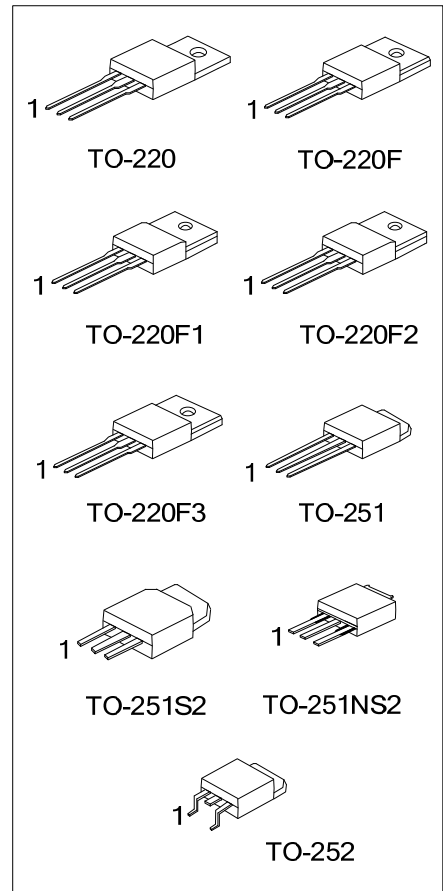
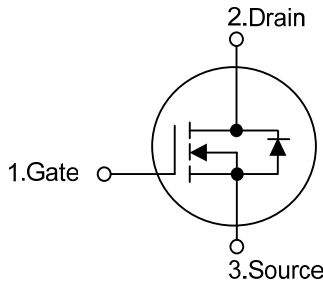
■ DESCRIPTION

The **UTC 7NM70** is a Super Junction MOSFET Structure and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and a high rugged avalanche characteristics. This power MOSFET is usually used at DC-DC, AC-DC converters for power applications.

■ FEATURES

- * $R_{DS(ON)} < 1.0\Omega @ V_{GS} = 10V, I_D = 3.5A$
- * Fast switching capability
- * Avalanche energy specified
- * Improved dv/dt capability, high ruggedness

■ SYMBOL



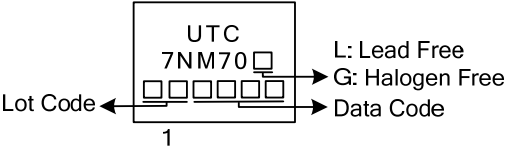
■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
7NM70L-TA3-T	7NM70G-TA3-T	TO-220	G	D	S	Tube
7NM70L-TF3-T	7NM70G-TF3-T	TO-220F	G	D	S	Tube
7NM70L-TF1-T	7NM70G-TF1-T	TO-220F1	G	D	S	Tube
7NM70L-TF2-T	7NM70G-TF2-T	TO-220F2	G	D	S	Tube
7NM70L-TF3T-T	7NM70G-TF3T-T	TO-220F3	G	D	S	Tube
7NM70L-TM3-T	7NM70G-TM3-T	TO-251	G	D	S	Tube
7NM70L-TMS2-T	7NM70G-TMS2-T	TO-251S2	G	D	S	Tube
7NM70L-TMN2-T	7NM70G-TMN2-T	TO-251NS2	G	D	S	Tube
7NM70L-TN3-R	7NM70G-TN3-R	TO-252	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>7NM70L-TA3-T</p>	<p>(1) T: Tube, R: Tape Reel (2) TA3: TO-220F, TF3: TO-220F, TF1: TO-220F1, TF2: TO-220F2, TF3T: TO-220F3, TM3: TO-251, TMS2: TO-251S2, TMN2: TO-251NS2, TN3: TO-252 (3) L: Lead Free, G: Halogen Free and Lead Free</p>
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MARKING



■ ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Drain-Source Voltage	V_{DSS}	700	V
Gate-Source Voltage	V_{GSS}	± 30	V
Continuous Drain Current	I_D	7.0	A
Drain Current Pulsed (Note 2)	I_{DM}	28	A
Avalanche Current (Note 2)	I_{AR}	2.4	A
Avalanche Energy, Single Pulsed (Note 3)	E_{AS}	29	mJ
Peak Diode Recovery dv/dt (Note 4)	dv/dt	4.2	V/ns
Power Dissipation	TO-220	142	W
	TO-220F/TO-220F1	48	W
	TO-220F3		
	TO-220F2	50	W
	TO-251/TO-251S2 TO-251NS2/TO-252	60	W
Junction Temperature	T_J	+150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

3. $L=10\text{mH}$, $I_{AS}=2.4\text{A}$, $V_{DD}=50\text{V}$, $R_G=25\ \Omega$, Starting $T_J=25^\circ\text{C}$.

4. $I_{SD} \leq 7.0\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J=25^\circ\text{C}$.

■ THERMAL DATA

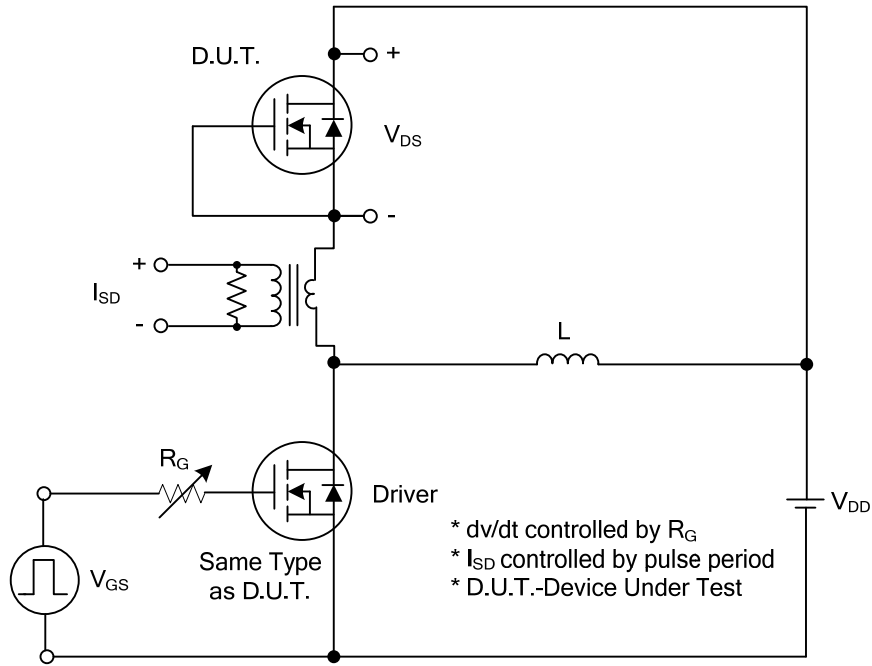
PARAMETER	SYMBOL	RATING	UNIT
Junction to Ambient	θ_{JA}	62.5	$^\circ\text{C/W}$
		110	
Junction to Case	θ_{JC}	0.88	$^\circ\text{C/W}$
		2.6	
		2.5	
		2.08	
		2.08	

■ ELECTRICAL CHARACTERISTICS ($T_J=25^\circ\text{C}$, unless otherwise specified)

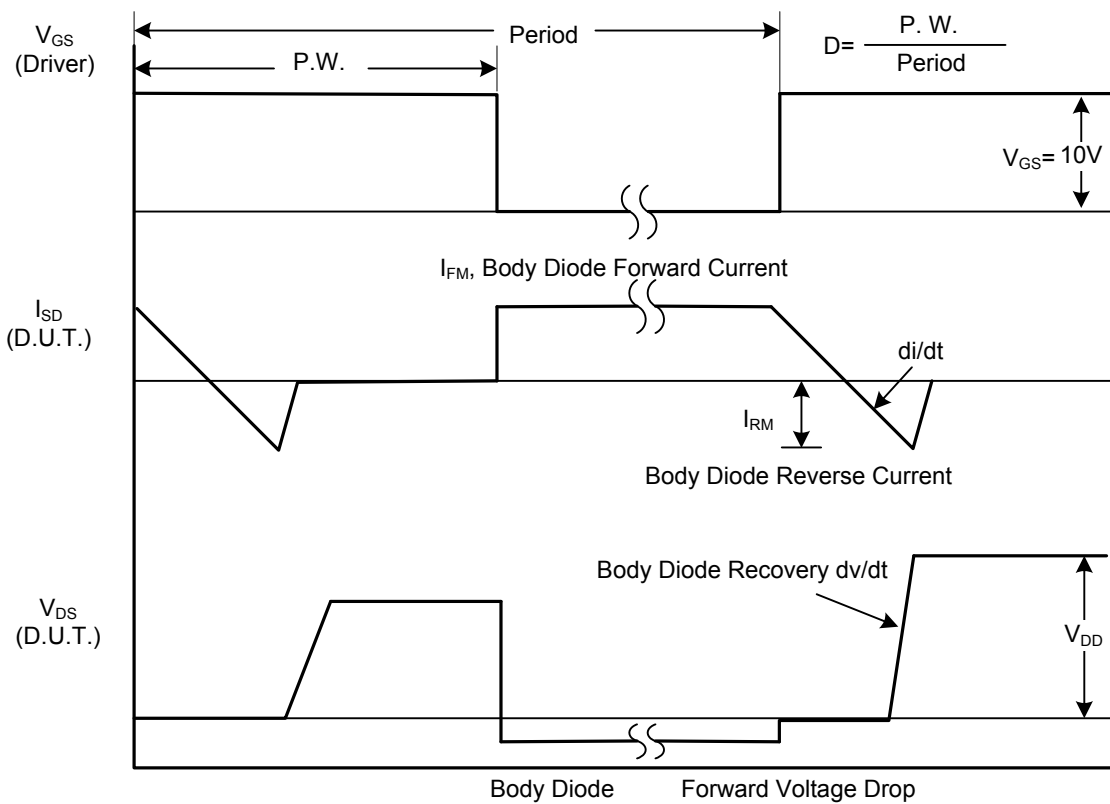
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = 250\mu A$	700			V
Drain-Source Leakage Current	I_{DSS}	$V_{DS} = 700V, V_{GS} = 0V$			10	μA
Gate-Source Leakage Current	Forward	I_{GSS}			100	nA
	Reverse					
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	2.5		4.5	V
Drain-Source ON-State Resistance	$R_{DS(ON)}$	$V_{GS} = 10V, I_D = 3.5A$			1.0	Ω
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{ISS}	$V_{GS}=0V, V_{DS}=25V, f=1.0MHz$		340		pF
Output Capacitance	C_{OSS}			120		pF
Reverse Transfer Capacitance	C_{RSS}			6.5		pF
SWITCHING CHARACTERISTICS						
Total Gate Charge (Note 1)	Q_G	$V_{DS}=50V, V_{GS}=10V, I_D=1.3A,$ $I_G=100\mu A$ (Note 1, 2)		19		nC
Gate to Source Charge	Q_{GS}			5		nC
Gate to Drain Charge	Q_{GD}			5.2		nC
Turn-ON Delay Time (Note 1)	$t_{D(ON)}$	$V_{DD}=30V, V_{GS}=10V,$ $I_D=0.5A, R_G=25\Omega$ (Note 1, 2)		50		ns
Rise Time	t_R			70		ns
Turn-OFF Delay Time	$t_{D(OFF)}$			140		ns
Fall-Time	t_F			65		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Maximum Body-Diode Continuous Current	I_S				7.0	A
Maximum Body-Diode Pulsed Current	I_{SM}				28	A
Drain-Source Diode Forward Voltage (Note 1)	V_{SD}	$I_S=7.0A, V_{GS}=0V$			1.4	V
Body Diode Reverse Recovery Time (Note 1)	t_{rr}	$I_S=7.0A, V_{GS}=0V,$ $di_F/dt = 100A/\mu s$		317		ns
Body Diode Reverse Recovery Charge	Q_{rr}			3.03		μC

Notes: 1. Pulse Test: Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$
2. Essentially independent of operating temperature

■ TEST CIRCUITS AND WAVEFORMS

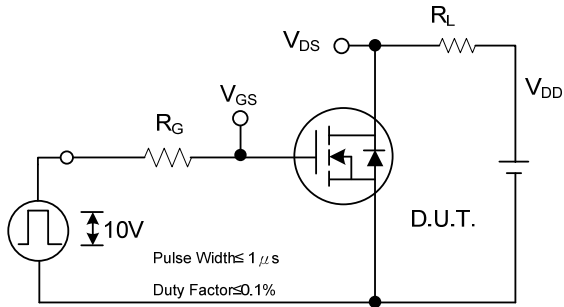


Peak Diode Recovery dv/dt Test Circuit

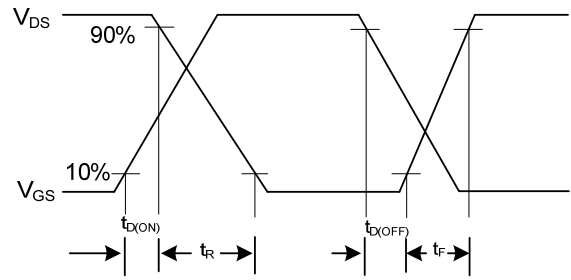


Peak Diode Recovery dv/dt Waveforms

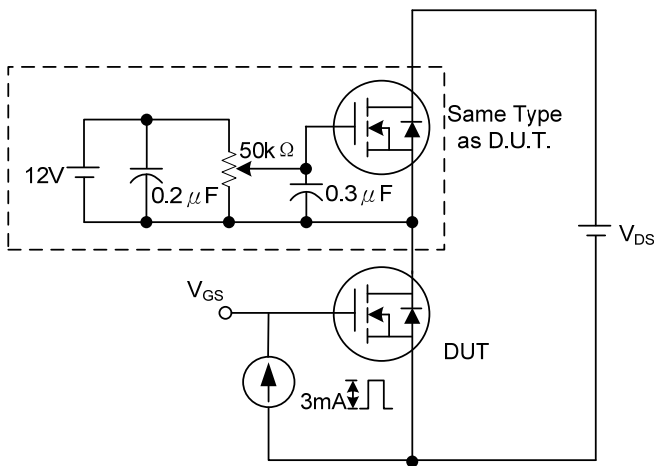
TEST CIRCUITS AND WAVEFORMS (Cont.)



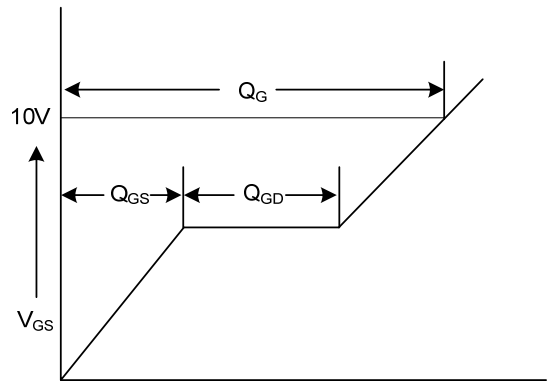
Switching Test Circuit



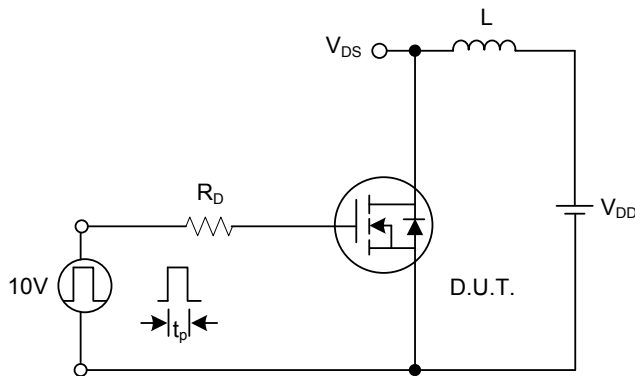
Switching Waveforms



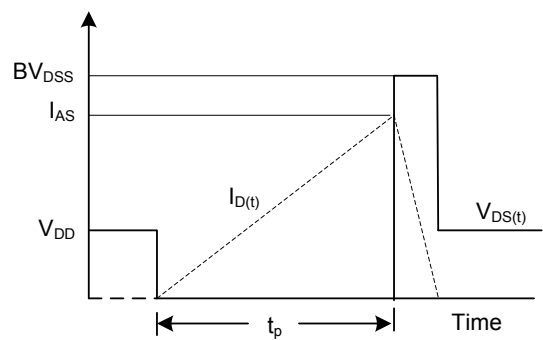
Gate Charge Test Circuit



Gate Charge Waveform

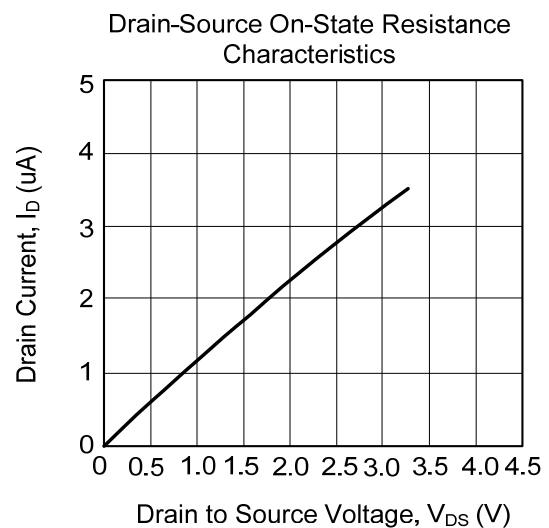
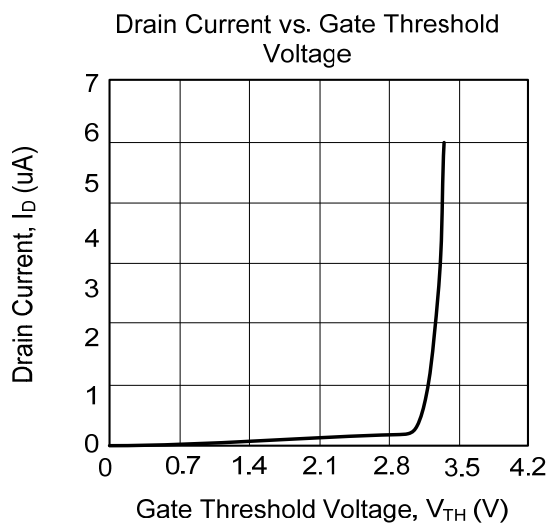
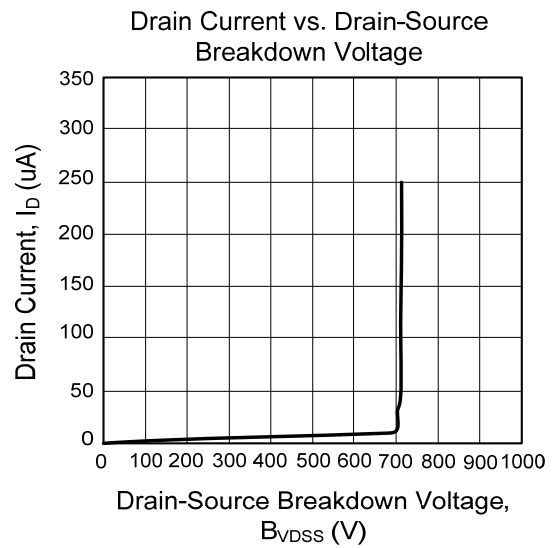
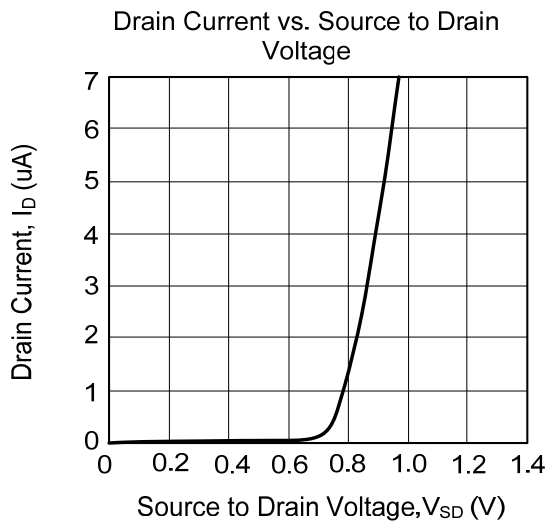


Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

■ TYPICAL CHARACTERISTICS



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